	1							R	EVIS	IONS										
LTR	ļ				I	ESCE	IPTI	ON]	DATE	(YR-M	O-DA)		APPI	ROVEL)
DIK)ESCF	CIPII	ON						DATE	(YR-M	O-DA)		APPI	ROVEL	
REV SHEET REV																				
									ļ <u>.</u>											-
SHEET REV STATE OF SHEETS				RE SH	V EET	i	1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A				PREP	ARED E		!		1	Di	EFENS	SE EL						ΓER		
STAI MICRO DRA THIS DRAWING FOR USE BY A AND AGENG DEPARTMENT	CIRC WING S IS A' LL DEP CIES O	CUIT G VAILAE PARTME	BLE NTS	DRAWING APPROVAL DATE				FEI SPI	EDBA	IRCU CK A	JITS AMPL	AYTON, OHIO 45444 VITS, LINEAR, CURRENT MPLIFIER, ULTRA HIGH PUT CLAMPING, MONOLITHIC								
AMSC N/A					94-08-08 EVISION LEVEL			SIZ A	E		E CO		į	5962	-94	577				
DESC FORM 193	<u> </u>									SHEE	T		<u>-</u>		1	OF	14			

UL 94

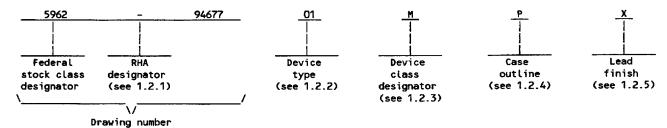
<u>DISTRIBUTION STATEMENT A</u>. Approved for public release; distribution is unlimited.

5962-E363-94

9004708 0009049 530 **9**

1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device class M RHA marked devices shall meet the MIL-I-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	HFA1130	Output clamping ultra high speed currrent feedback amplifier

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class Device requirements documentation

M Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883

microcircuits in accordance with 1.2.1 of HIL-SiD-003

Q or V Certification and qualification to MIL-I-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
P	GDIP1-T8 or CDIP2-T8 CQCC1-N2O	8	Dual-in-line package
2		20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94677
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 2

DESC FORM 193A JUL 94

9004708 0009050 252 🞟

1.3 Absolute maximum ratings. 1/ Voltage between V+ and V-Differential input voltage ----- 5 V Voltage at either input terminal ----- V+ to V-Output current (50% duty cycle) ---- ±55 mA Maximum power dissipation at +75°C: Case outline P ----- 0.87 W Case outline 2 ----- 1.33 W Power dissipation derating factor above +75°C: Case outline P ----- 8.7 mW/°C Case outline 2 ---- 13.3 mW/°C Junction temperature (T_1) ----+175°C Lead temperature (soldering 10 sec) -----+300°C 1.4 Recommended operating conditions. R_L 2. APPLICABLE DOCUMENTS 2.1 Government specification, standards, bulletin, and handbook. Unless otherwise specified, the following specification, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein. **SPECIFICATION** MILITARY MIL-I-38535 - Integrated Circuits, Manufacturing, General Specification for. STANDARDS MILITARY MIL-STD-883 - Test Methods and Procedures for Microelectronics. MIL-STD-973 - Configuration Management. MIL-STD-1835 - Microcircuit Case Outlines. BULLETIN MILITARY MIL-BUL-103 - List of Standardized Military Drawings (SMD's). HANDBOOK MILITARY MIL-HDBK-780 - Standardized Military Drawings. (Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.) Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability. STANDARD SIZE 5962-94677 MICROCIRCUIT DRAWING A DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 REVISION LEVEL SHEET 3

DESC FORM 193A JUL 94 2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V and herein.
 - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.
 - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Test circuit. The test circuit shall be as specified on figure 2.
 - 3.2.4 Test waveforms. The test waveforms shall be as specified on figure 3.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.
- 3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M, the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M</u>. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M</u>. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-I-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.

STANDARD MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-94677
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 4

DESC FORM 193A JUL 94

■ 9004708 0009052 025 **■**

Test	Symbol	Condition $ \begin{array}{ccc} & & & & & & \\ & & & & & \\ & & & -55^{\circ}C \leq T_{A} \leq 4 \\ & & & & & \\ & & & & & \\ & & & & & $	+125°C	Group A subgroups	Device type	Limits		Unit	
	<u> </u>	V _{SUPPLY} = ±5 unless otherwise s	specified			 Min 	Max		
Input offset voltage	V ₁₀	 v _{cm} = 0 v 	 	2,3	ALL	 <u>-6</u> -10	6 10	mV	
Common mode rejection ratio	CMRR	ΔV _{CM} = ±2 V V+ = 3 V, V- = -7 V V+ = 7 V, V- = -3 V		1 2,3	ALL	40 38		dB	
Power supply rejection ratio	 PSRRP 	 	-5 V	2,3	ALL	45 42	 	dB	
	 PSRRN 	 	25 V 75 V	1 2,3	ALL	45 42		dB	
Non-inverting input (+IN) current	I _{BSP}	v _{cm} = 0 v		1 2,3	ALL	 40 65	 <u>40</u> 65	 µA 	
+IN current common mode sensitivity	 CMS _{IBP} 	ΔV _{CM} = ±2 V V+ = 3 V, V- = -7 V V+ = 7 V, V- = -3 V		1 2,3	ALL		 <u>40</u> 50	 µА/V 	
+IN resistance	 +R _{IN} 	<u>2</u> /		1 2,3	ALL	25 20		 kΩ 	
Inverting input (-IN) current	 ^I BSN 	v _{cm} = 0 v		1 2,3	ALL	<u>-50</u> -75	50 75	 μΑ 	
-IN current common mode sensitivity		ΔV _{CM} = ±2 V V+ = 3 V, V- = -7 V V+ = 7 V, V- = -3 V		1 2,3	ALL		7 10	 μΑ/V	
-IN current power supply sensitivity	PPSS _{IBN}	ΔV _{SUPPLY} = ±1.25 V V+ = 6.25 V, V- = - V+ = 3.75 V, V- = -	5 V	1 2,3	ALL		15 27	μΑ/V 	
	NPSS _{IBN}	ΔV _{SUPPLY} = ±1.25 V V+ = 5 V, V- = -6.2 V+ = 5 V, V- = -3.7	 5 V 5 V	1 2,3	ALL		15 27	 µA/V 	
Output voltage swing	V _{OP100}	$A_V = -1$ $R_L = 100 \Omega$ V_{IN}	= -3.5 V = -3.0 V	1 2,3	ALL	<u>3</u> 2.5		 V 	
	V _{ON100}	$A_V = -1$ v_{IN} $R_L = 100 \Omega$ v_{IN}	= +3.5 V = +3.0 V	1 2,3	ALL		-3 -2.5	 V 	
See footnotes at end of table.							**************************************		
STAND MICROCIRCUI	T DRAW	ING	SIZE				59	62-94677	
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444			REV	ISION	LEVEL	SHE	 ЕТ		

5

DESC FORM 193A JUL 94

9004708 0009053 Tbl 📟

Test	Symbol	 Condition -55°C ≤ T _A ≤ +	s 125°C	Group A subgroups	Device type	 L1 	mits	Unit
		-55°C ≤ T _A ≤ + V _{SUPPLY} = ±5 unless otherwise s	V <u>1</u> / pecified			 Min	Max	<u> </u>
Output voltage swing	V _{OP50}	$\begin{vmatrix} A_V = -1 & \underline{V}_{IN} \\ R_L = 50 \Omega & V_{IN} \end{vmatrix}$	= -3.0 V = -2.0 V	1,2	ALL	2.5 1.5		 v
	V _{ON50}	$\begin{vmatrix} A_{V} = -1 & \frac{V}{IN} \\ R_{L} = 50 \Omega & V_{IN} \end{vmatrix}$	= +3.0 V = +2.0 V	1,2 3	ALL	 	-2.5 -1.5	V
Output current	+ ¹ out	<u> 3</u> /		<u>1,2</u> 3	ALL	50 30		mA
	TucI-] <u>3</u> /		<u>1,2</u> 3	ALL	 	-50 -30	mA
Quiescent power supply current	Icc	R _L = 100 Ω		1 2,3	ALL	14	<u>26</u> 33	mA
	IEE	R _L = 100 Ω		1 2,3	ALL	<u>-26</u> -33	-14	mA.
Clamp accuracy	V _H CLMP	A _V = -1, V _{IN} = -2 V V _H = 1 V		<u>1</u> 2,3	ALL	<u>-125</u> -200	125 200	mV
	V _L CLMP	 A _V = -1, V _{IN} = +2 V V _L = -1 V		2,3	ALL	 -125 -200	125 200	mV
Clamp input current	VHBIAS	v _H = 1 v		1 2,3	ALL		200	μA
	V_BIAS	 v _H = -1 v		1 2,3	ALL	 <u>-200</u> -300		μΑ
-3dB Bandwidth	BW(-1)	A _V = -1, R _F = 430 Ω V _{OUT} = 200 mV _{P-P}	<u>5</u> /	4	ALL	300		MHz
2 /	BW(+1)	A _V = +1, R _F = 510 Ω V _{OUT} = 200 mV _{P-P}	<u>5</u> /	4	ALL	550		MHz
	BW(+2)	A _V = +2,	5/	4	ALL	350		MHz
See footnotes at end of ta	ble.	1			.1	ı		I
MICROCIR			SIZI	E			59	62-9467
	ICROCIRCUIT DRAWING ELECTRONICS SUPPLY CENTER AYTON, OHIO 45444			RE'	VISION	LEVEL	SHE	ET

6

DESC FORM 193A JUL 94

■ 9004708 0009054 9T8 **■**

Test	Symbol	Conditions $\begin{array}{ccc} & & & & & & \\ & -55^{\circ}C & \leq & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & \\ & & & \\ & & & \\ & & \\ & & & \\ & & & \\ & & \\ & & & \\ & & \\ & & \\ & & & \\ & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\$	Group A subgroups	Device type	Limits		Unit
		unless otherwise specified			Min	Max	
Gain flatness	GF30	A _V = +2, R _F = 510 Ω, V _{OUT} = 200 mV _{P-P} , f≤ 30 MHz	4	All		±0.04	ďВ
	 GF50 	$ A_V = +2, R_F = 510 \Omega$ $ V_{OUT} = 200 \text{ mV}_{P-P}, f \le 50 \text{ MHz}$	4	ALL	 	±0.10	dΒ
	GF100	A _V = +2, R _F = 510 Ω V _{OUT} = 200 mV _{P-P} , f≤ 100 MHz	4	 All 		±0.30	dВ
Slew rate	 +SR(+1) 	 A _V = +1, R _F = 510 Ω V _{OUT} = 5 V _{P-P} <u>6</u> /	4	ALL	1200	1	V/µs
	 -SR(+1)	 A _V = +1, R _F = 510 Ω V _{OUT} = 5 V _{P-P} <u>6</u> /	4	ALL	 1100 		V/μs
	+SR(+2)	 A _V = +2, V _{OUT} = 5 V _{P-P} <u>6</u> /	4	ALL	1650		V/µs
	-SR(+2)	 A _V = +2, v _{OUT} = 5 v _{P-P} <u>6</u> /	4	ALL	1500		V/µs
Rise and fall time	T _R	$ A_V = +2, V_{OUT} = 0.5 V_{P-P} \underline{6}/$	9	ALL		1 1	ns
<u>4</u> /	T _F	 A _V = +2, V _{OUT} = 0.5 V _{P-P} <u>6</u> /	9	All		1 1	ns
Overshoot	+os	 A _V = +2, V _{OUT} = 0.5 V _{P-P} <u>7</u> /	4	ALL		25	%
<u>4</u> /	 -os	 A _V = +2, V _{OUT} = 0.5 V _{P-P} <u>7</u> /	4	All		20	%
Settling time	TS(0.1)	 A _V = +2, R _F = 510 Ω V _{OUT} = 2 V to 0 V, to 0.1%	9	ALL		 20 	ns
	T\$(.05)	A _V = +2, R _F = 510 Ω V _{OUT} = 2 V to 0 V, to 0.05%	9	ALL		 33 	ns

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-94677
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 7

DESC FORM 193A JUL 94

■ 9004708 0009055 834 ■

Test	Symbol	Conditions $-55^{\circ}C \leq T_{A} \leq +125^{\circ}C$	Group A subgroups	Device type	Limits		Unit
		$-55^{\circ}C \le T_A \le +125^{\circ}C$ $V_{SUPPLY} = \pm 5 V $			Min	Max	
2nd Harmonic Distortion	HD2(30)	 A _V = +2, V _{OUT} = 2 V _{P-P} , f = 30 MHz	4	ALL		-48	dBc
	 HD2(50) 	 A _V = +2, V _{OUT} = 2 V _{P-P} , f = 50 MHz	4	ALL		-45	dBc
	 HD2(100) 	 A _V = +2, V _{OUT} = 2 V _{P-P} , f = 100 MHz	4	ALL		-35	dBc
5nd Harmonic Distortion	HD3(30)	A _V = +2, V _{OUT} = 2 V _{P-P} , f = 30 MHz	4	ALL		 -6 5	dBc
-	HD3(50)	A _V = +2, V _{OUT} = 2 V _{P-P} , f = 50 MHz	4	ALL		-60	dBc
	HD3(100)	A _V = +2, V _{OUT} = 2 V _{P-P} , f = 100 MHz	 4 	ALL		-40	 dBc

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94677
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 8

■ 9004708 0009056 770 ■

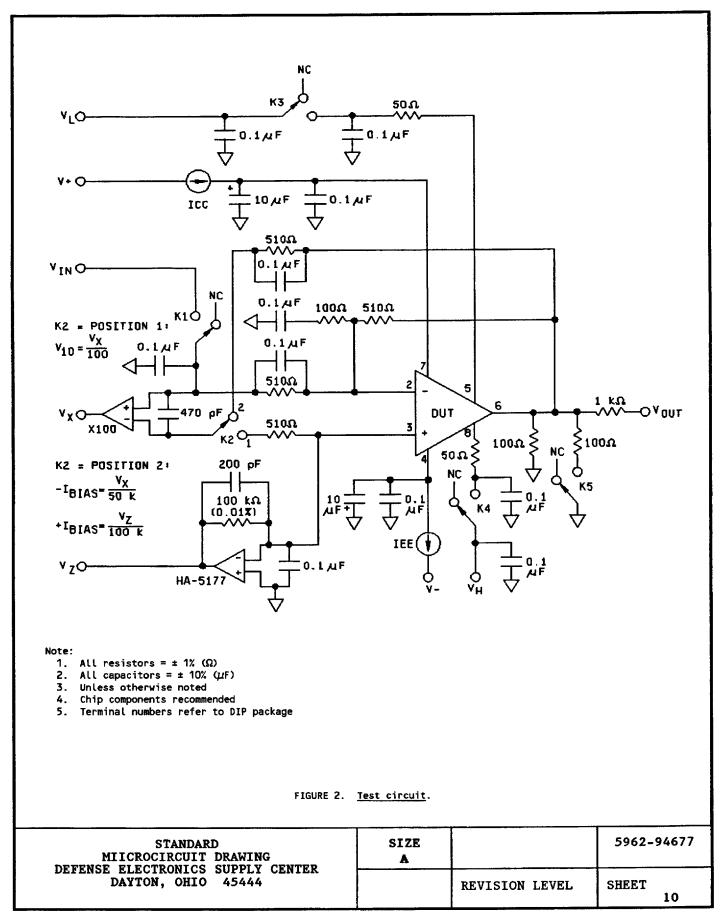
^{1/.} A_V = +1, R_F = 510 Ω , R_{SOURCE} = 0 Ω , R_L = 100 Ω , V_{OUT} = 0 V unless otherwise specified. See figure 2. 2/. Guaranteed from +IN common mode rejection test, by: $+R_{IN}$ = 1/cMS $_{IBP}$. 3/. Guaranteed from V_{OUT} test with R_L = 50 Ω , by: I_{OUT} = $V_{OUT}/50$ Ω . 4/. Shall be guaranteed, if not tested, to the specified limits in table I. 5/. A_V = +2, R_F = 360 Ω , R_L = 100 Ω unless otherwise specified. See figure 3. 6/. Measured between 10% and 90% points. 7/. For 200 ps input transition times. Overshoot decreases as input transition time increase, especially for A_V = +1.

Device type	0	1
Case outlines	P	2
Terminal number	Terminal	Terminal
1 1	NC	NC
2	-IN	NC
3	+IN	NC
j 4 j	V-	NC
5	V,	-IN
6	τΰο	NC NC
7	V+	+IN
8	v _H	NC I
9		NC I
10		V-
j 11 j		i v _e i
12		ี่ที่เ
13		NC I
14		NC I
15		OUT
16		NC
17		V+
18		۸ ^H
19		NC I
20		NC

FIGURE 1. <u>Terminal connections</u>.

STANDARD MIICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-94677
		REVISION LEVEL	SHEET 9

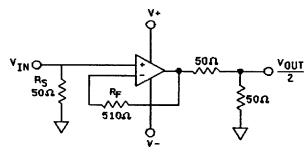
9004708 0009057 607

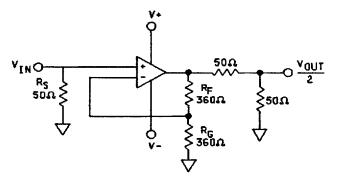


9004708 0009058 543

Av = +1 TEST CIRCUIT



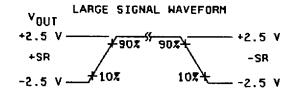




Note:

1. $V_S = \pm 5$ V, $A_V = +1$ 2. $R_S = 50$ Ω 3. $R_L = 100$ Ω for small and large signals

1. $V_S = \pm 5$ V, $A_V = +2$ 2. $R_S^2 = 50 \Omega$ 3. $R_L^2 = 100 \Omega$ for small and large signals



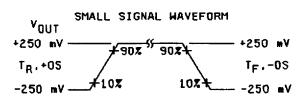


FIGURE 3. Test waveforms.

STANDARD MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-94677
		REVISION LEVEL	SHEET 11

DESC FORM 193A **JUL 94**

9004708 0009059 48T 📟

4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device class M.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125$ °C, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein. Interim test is optional at the discretion of the manufacturer.

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
- b. Interim and final electrical test parameters shall be as specified in table II herein. Interim test is optional at the discretion of the manufacturer.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.
- 4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 5, 6, 7, 8, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.
- 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table II nerein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

STANDARD MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-94677
		REVISION LEVEL	SHEET 12

DESC FORM 193A JUL 94

■ 9004708 0009060 1T1 **■**

TABLE II. <u>Electrical test requirements</u>.

Test requirements	Subgroups (in accordance with MIL-STD-883, TM 5005, table I)	Subgroups (in accordance with MIL-I-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
final electrical parameters (see 4.2)	1,2,3 1/	1,2,3 1/	1,2,3 1/
Group A test requirements (see 5.4)	1,2,3,4,9, 2/	1,2,3,4,9	1,2,3,4,9
Group C end-point electrical parameters (see 4.4)	1	1	1,2,3,4,9
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)			
AND THE PERSON NAMED IN COLUMN TWO IS NOT THE PERSON NAMED IN COLUMN TWO IS NAMED IN COLUMN TWO I		1	

- 1/ PDA applies to subgroup 1.
- 2/ Subgroups 4 and 9 are guaranteed if not tested.
- 4.4.2.2 <u>Additional criteria for device classes Q and V</u>. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-I-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
- 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes Q and V shall be M, D, R, and H and for device class M shall be M and D.
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-I-38535, appendix A, for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

STANDARD MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-94677
		REVISION LEVEL	SHEET 13

9004708 0009061 038

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.

6 NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 <u>Substitutability</u>. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5270, or telephone (513) 296-5377.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-I-38535 and MIL-STD-1331.
- 6.6 One part one part number system. The one part one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document <u>listing</u>
New MIL-H-38534 Standard Microcircuit Drawings	5962-XXXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standard Microcircuit Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standard Microcircuit Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

- 6.7.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

STANDARD MICROCIRCUIT DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-94677
		REVISION LEVEL	SHEET 14

DESC FORM 193A JUL 94

■ 9004708 0009062 T74 **■**

46565